



2813
\$

12/EXT-2
Elec/a
1.5 step to
1/16/03

TECHNOLOGY CENTER 2800
DEC 17 2002
RECEIVED

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei YAMAZAKI et al.

Art Unit : 2813

Serial No. : 09/769,765

Examiner : Laura Schillinger

Filed : January 26, 2001

Title : SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

Commissioner for Patents
Washington, D.C. 20231

RESPONSE TO RESTRICTION/ELECTION REQUIREMENT

In response to the action mailed September 16, 2002, please amend the application as noted.

In the claims:

Please cancel claims 1-16 and 25-47 without prejudice or disclaimer.

Please amend claims 17-19 and 21 as follows:

how
B1
the
com

17. (Amended) A semiconductor device comprising:
a first semiconductor layer and a second semiconductor layer on an insulating surface;
a first insulating film on the first semiconductor layer and on the second semiconductor layer;
a first electrode on the first insulating film, overlapping the first semiconductor layer;
a second electrode on the first insulating film, overlapping the second semiconductor layer;
a source wiring on the first insulating film;
a second insulating film covering the first electrode and the source wiring;
a gate wiring on the second insulating film, connected to the first electrode;
a connection electrode on the second insulating film, connected to the source wiring and the first semiconductor layer; and
a pixel electrode on the second insulating film, connected to the first semiconductor layer;
wherein at least one end of the pixel electrode overlays the source wiring with the second insulating film interposed therebetween.